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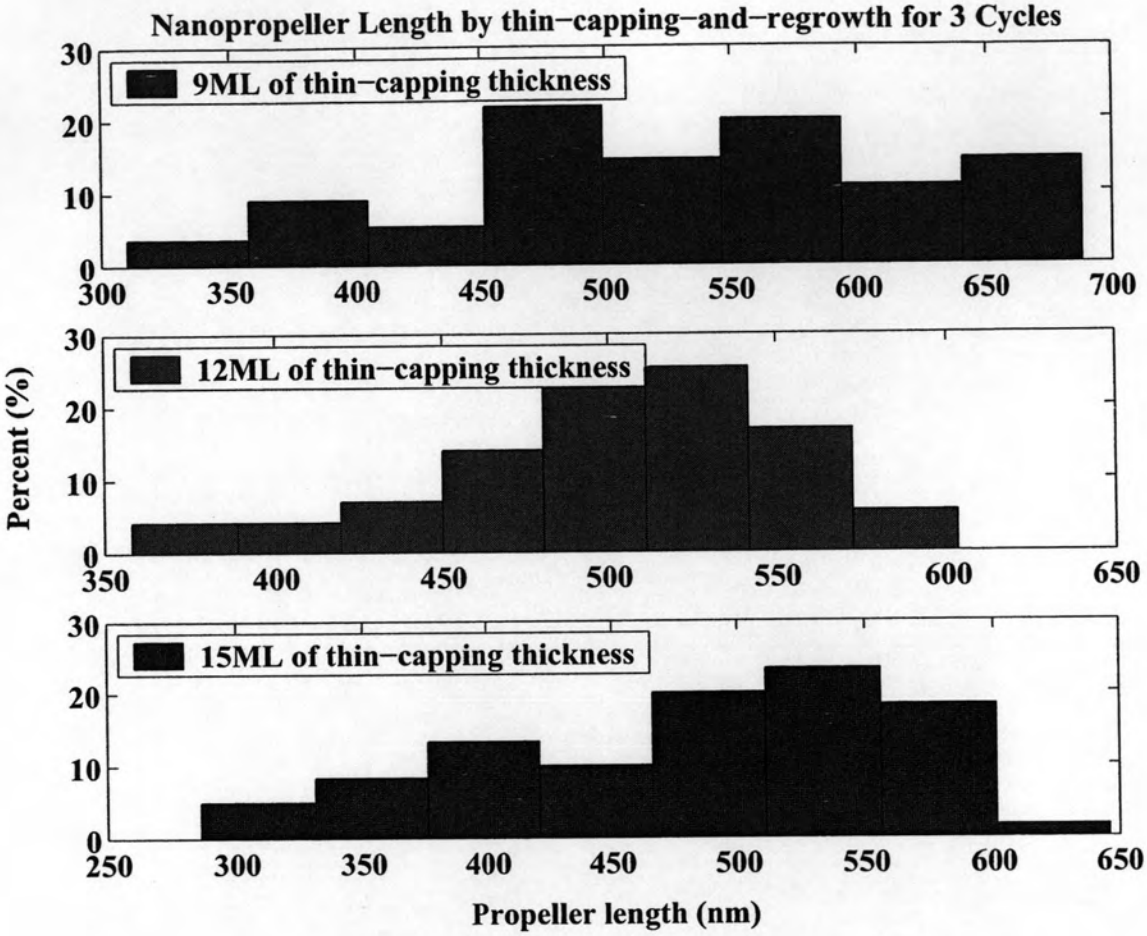
Appendix

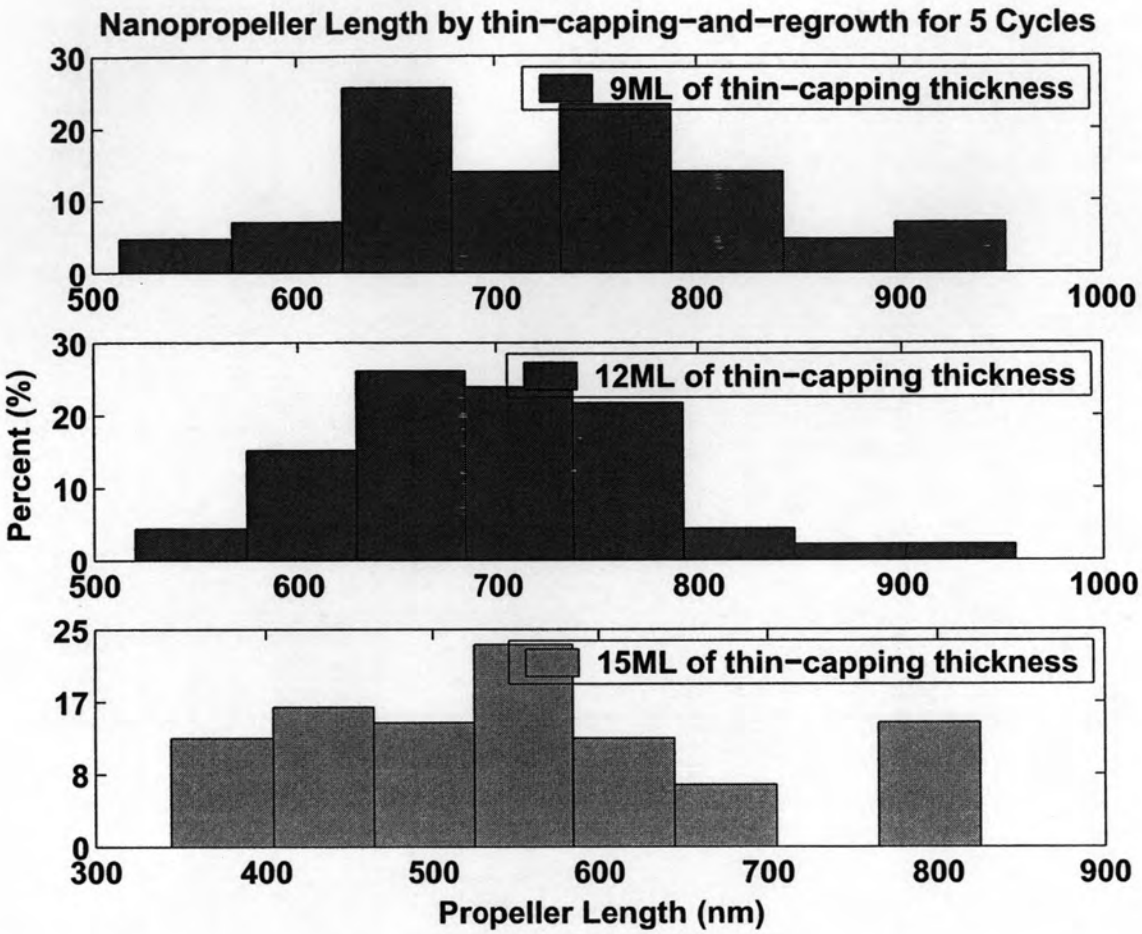
List of Proceedings

1. "Long Chains of Self-Assembled InAs Quantum Dot Molecules by Modified MBE Growth Technique", S. Ruangdet, N. Budsayaplakorn, S. Thainoi, S. Kanjanachuchai and S. Panyakeow, Proceeding of MBE2006 (14th International Conference on Molecular Beam Epitaxy), Tokyo, (2006)

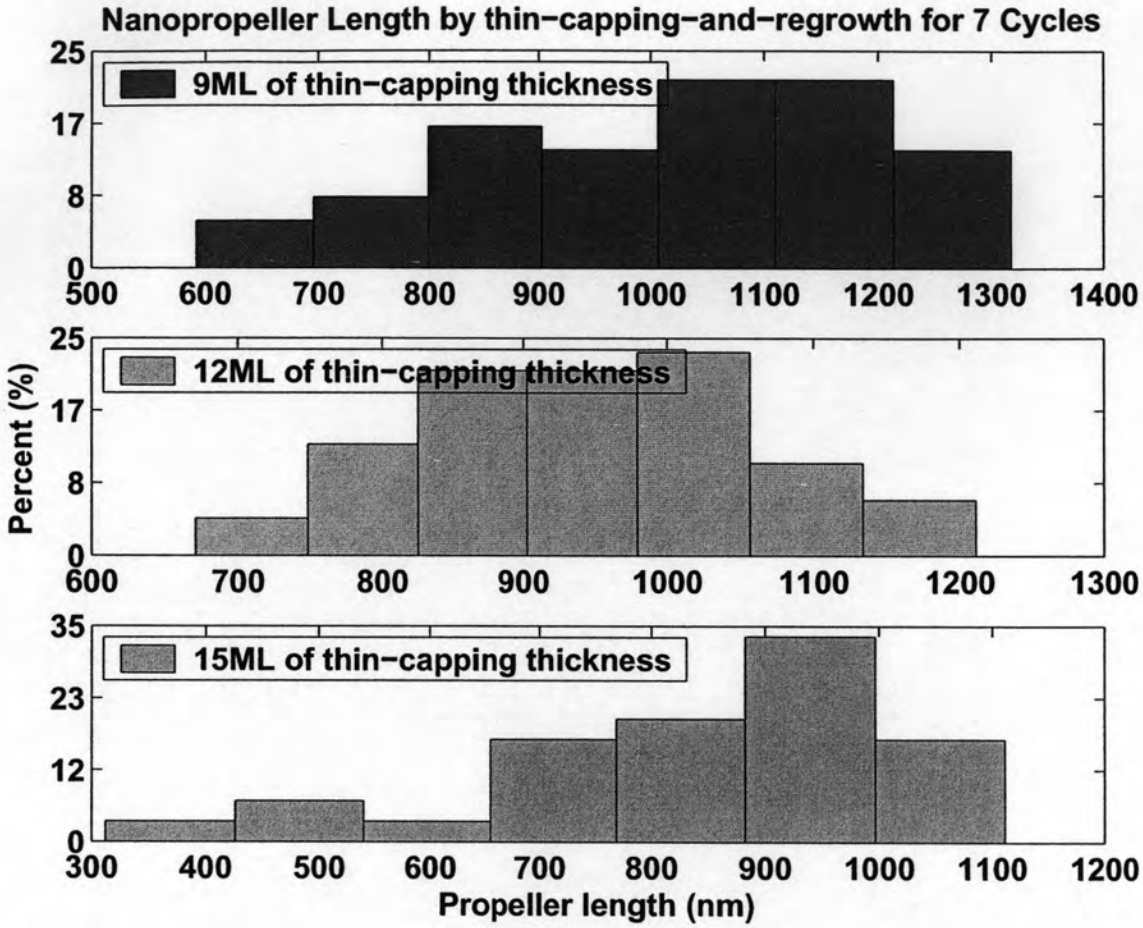
2. "Quantum Dot Molecule Chains and Their Polarization Photoluminescence", Nuttawut Budsayaplakorn, Supachok Thainoi and Somsak Panyakeow, ECTI-CON 2007, Mae-Fah Luang University, Chiang Rai, Thailand, (May 9-12, 2007)



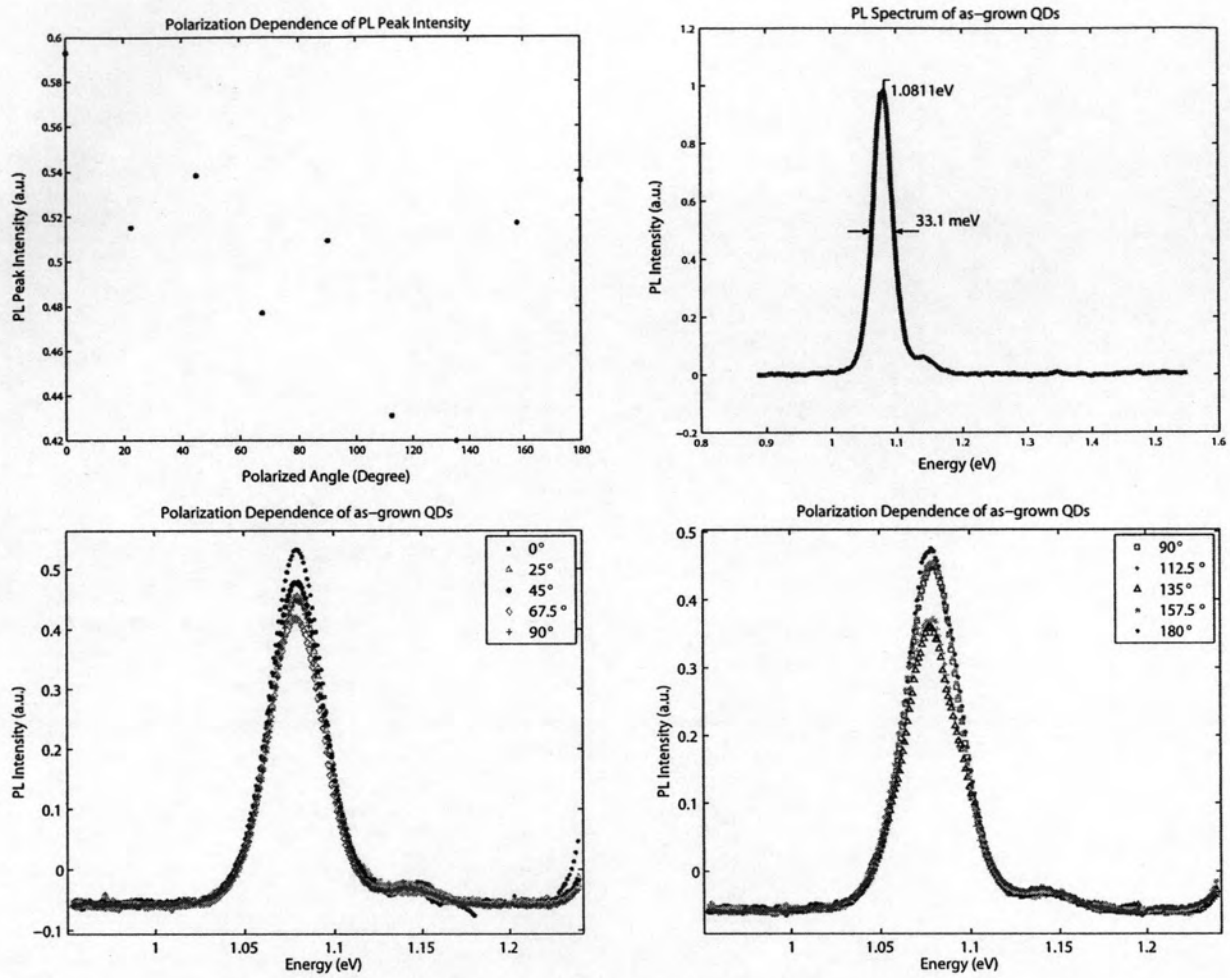
Length distribution of nanopropeller from 3 cycles of thin-capping-and-regrowth for thin-capping thickness of 9, 12, 15 ML



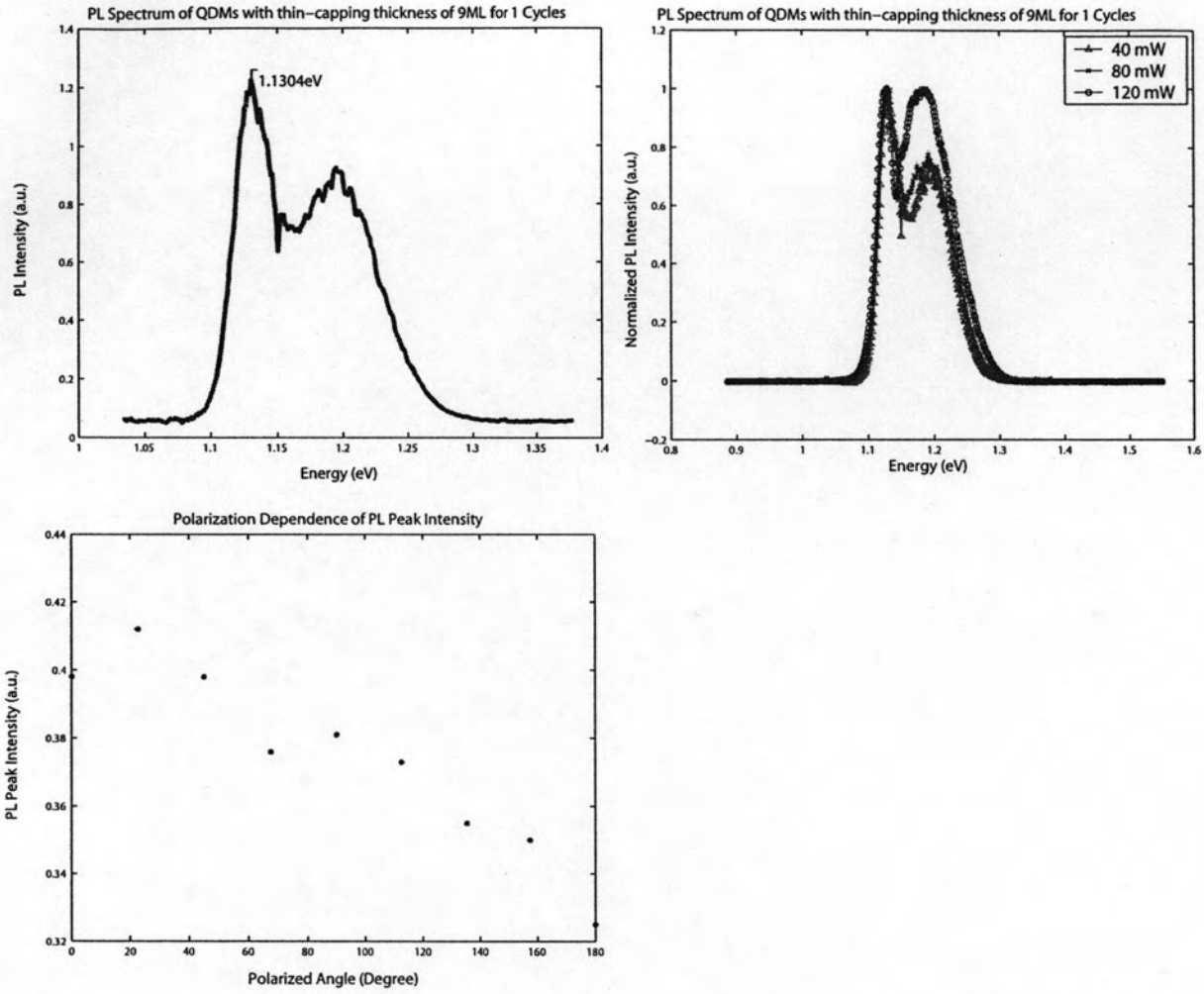
Length distribution of nanopropeller from 5 cycles of thin-capping-and-regrowth for thin-capping thickness of 9, 12, 15 ML



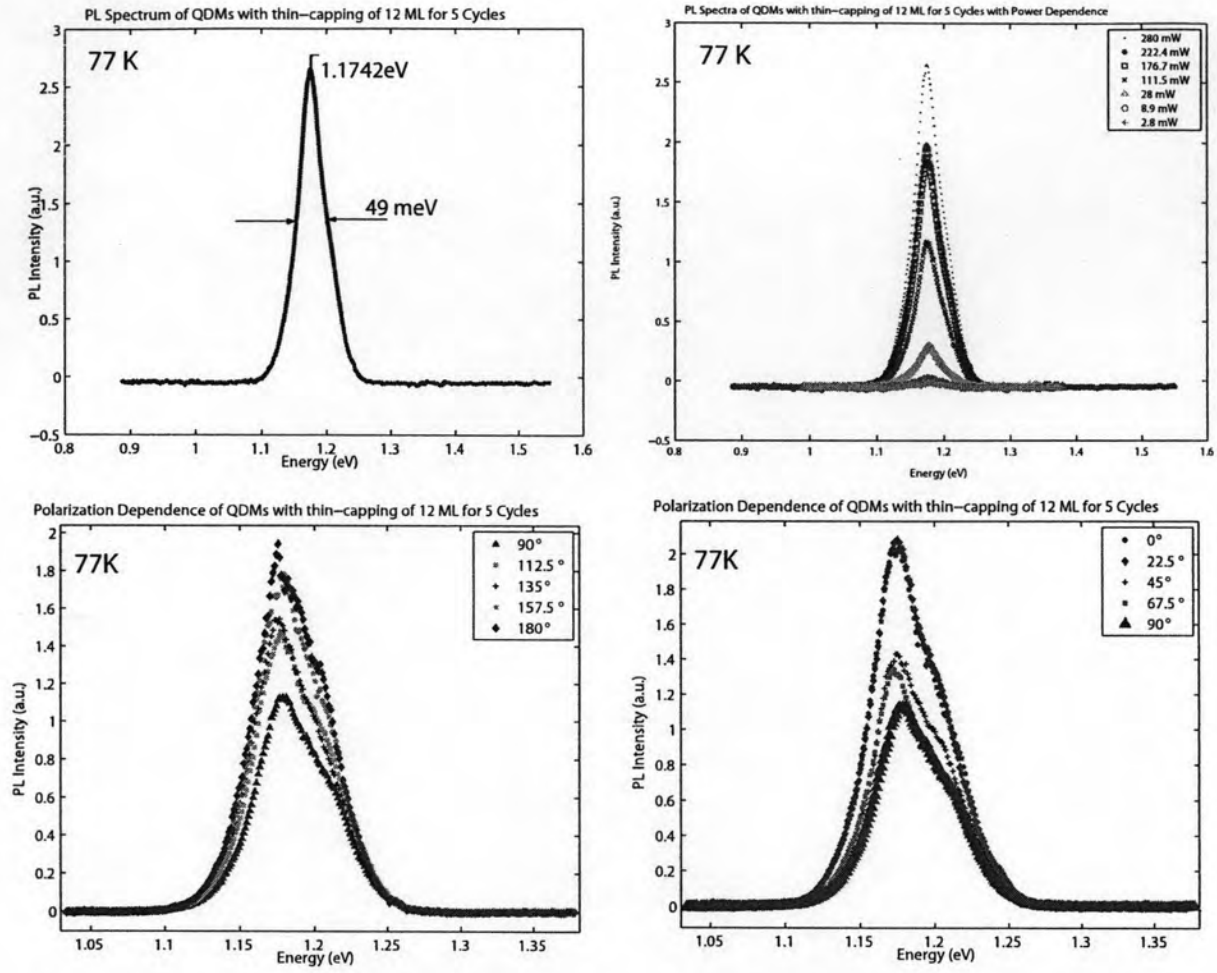
Length distribution of nanopropeller from 7 cycles of thin-capping-and-regrowth for thin-capping thickness of 9, 12, 15 ML



PL measurement results of as-grown QDs with no observation of polarization dependence



PL measurement results of QDMs from 1 cycle of 9ML-thin-capping-and-regrowth with no observation of polarization dependence



Results of PL measurement, excitation-power dependence measurement and polarization dependence measurement of QDMs from 5 cycle of 12ML-thin-capping-and-regrowth

Vitae

Nuttawut Budsayaplakorn was born in Saraburi , Thailand on July 6, 1983. He graduated from Thaweethapisek school in March 2001. In June 2001, He entered Chulalongkorn University and received the Bachelor of Engineering in field of Electrical Engineering in May 2005. He was further her study in June 2005, as a master student.